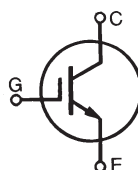


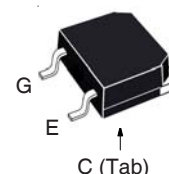
High Voltage IGBT

IXGT6N170AHV



$$\begin{aligned} V_{CES} &= 1700V \\ I_{C25} &= 6A \\ V_{CE(sat)} &\leq 7.0V \\ t_{fi(typ)} &= 32ns \end{aligned}$$

TO-268



G = Gate C = Collector
E = Emiiter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^{\circ}C$ to $150^{\circ}C$	1700	V
V_{CGR}	$T_J = 25^{\circ}C$ to $150^{\circ}C$, $R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^{\circ}C$	6	A
I_{C110}	$T_C = 110^{\circ}C$	3	A
I_{CM}	$T_C = 25^{\circ}C$, 1ms	14	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^{\circ}C$, $R_G = 33\Omega$	$I_{CM} = 12$	A
(RBSOA)	Clamped Inductive Load	$0.8 \cdot V_{CES}$	
t_{sc}	$V_{GE} = 15V$, $V_{CE} = 1200V$, $T_J = 125^{\circ}C$	10	μs
(SCSOA)	$R_G = 33\Omega$, Non Repetitive		
P_C	$T_C = 25^{\circ}C$	75	W
T_J		-55 ... +150	$^{\circ}C$
T_{JM}		150	$^{\circ}C$
T_{stg}		-55 ... +150	$^{\circ}C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^{\circ}C$
T_{SOLD}	Plastic Body for 10 seconds	260	$^{\circ}C$
Weight		4	g

Symbol	Test Conditions ($T_J = 25^{\circ}C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ $T_J = 125^{\circ}C$			10 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 3A$, $V_{GE} = 15V$, Note 1 $T_J = 125^{\circ}C$		5.4	7.0 V V

Features

- High Blocking Voltage
- High Voltage Package

Advantages

- High Power Density
- Easy to Mount

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines

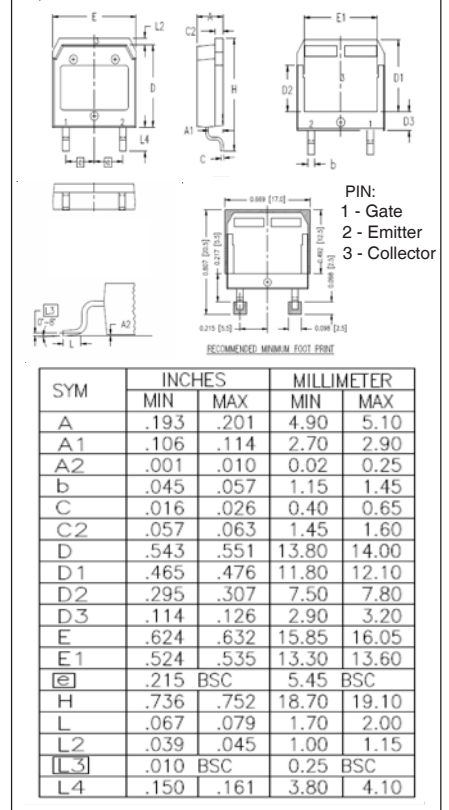
Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.
g_{fs}	$I_C = 6\text{A}, V_{CE} = 20\text{V}, \text{Note 1}$	2.0	3.5	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		390	pF
C_{oes}			20	pF
C_{res}			7	pF
$Q_{g(on)}$	$I_C = 6\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		18.5	nC
Q_{ge}			2.8	nC
Q_{gc}			8.2	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 6\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 33\Omega$ Note 2		46	ns
t_{ri}			40	ns
E_{on}			0.59	mJ
$t_{d(off)}$			220	ns
t_{fi}			32	ns
E_{off}			0.18	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 6\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 33\Omega$ Note 2		48	ns
t_{ri}			43	ns
E_{on}			0.62	mJ
$t_{d(off)}$			230	ns
t_{fi}			41	ns
E_{off}			0.25	mJ
R_{thJC}				1.65 $^\circ\text{C/W}$

TO-268 (VHV) Outline



Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

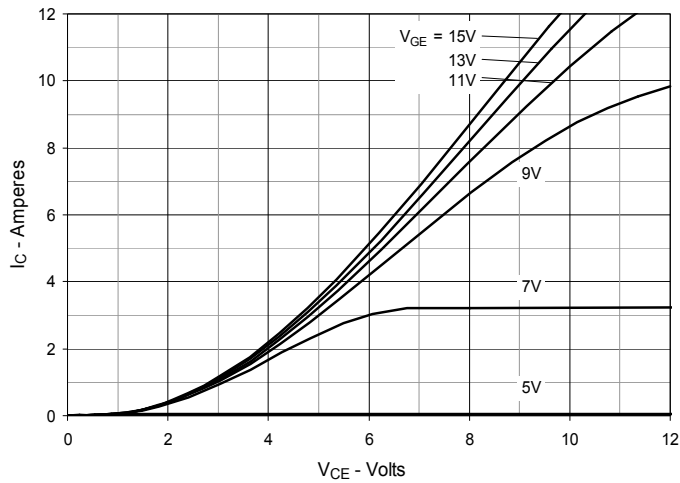


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

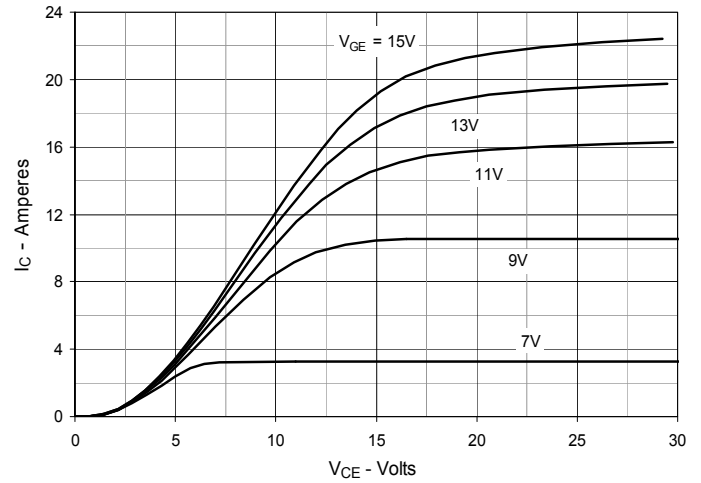


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

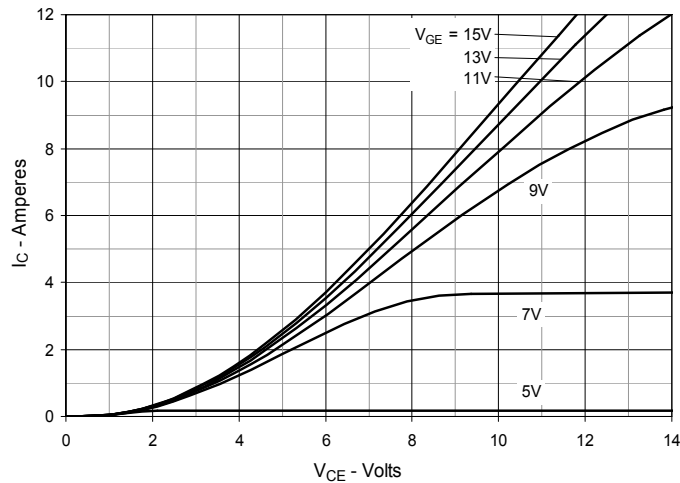


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

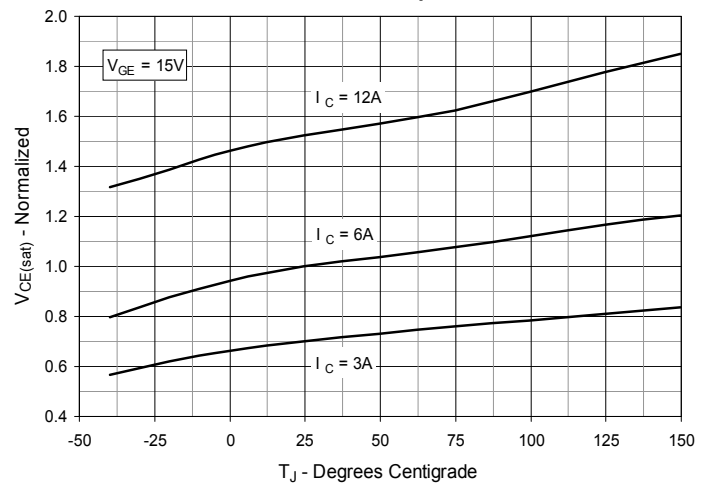


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

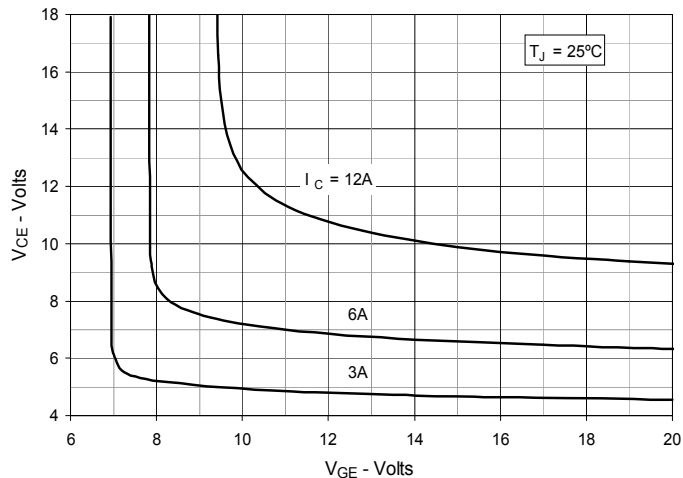


Fig. 6. Input Admittance

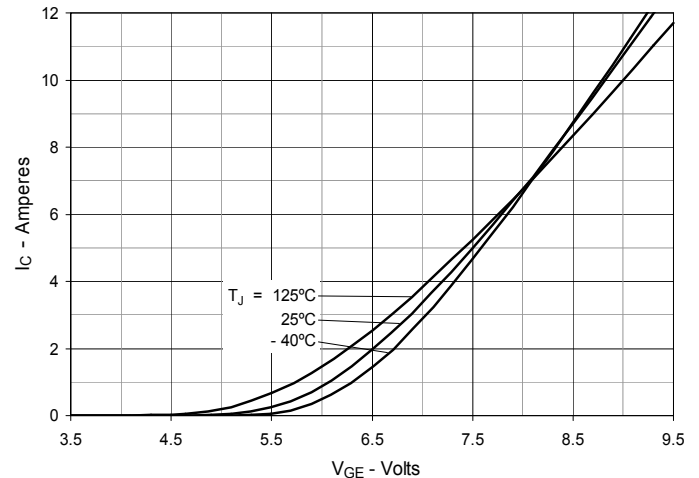


Fig. 7. Transconductance

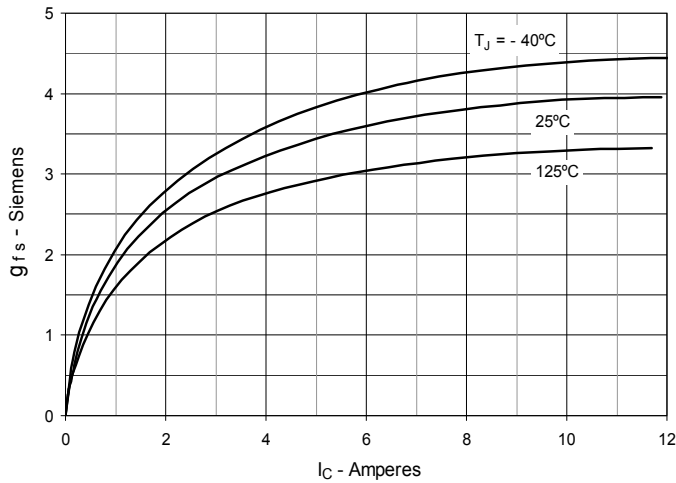


Fig. 8. Gate Charge

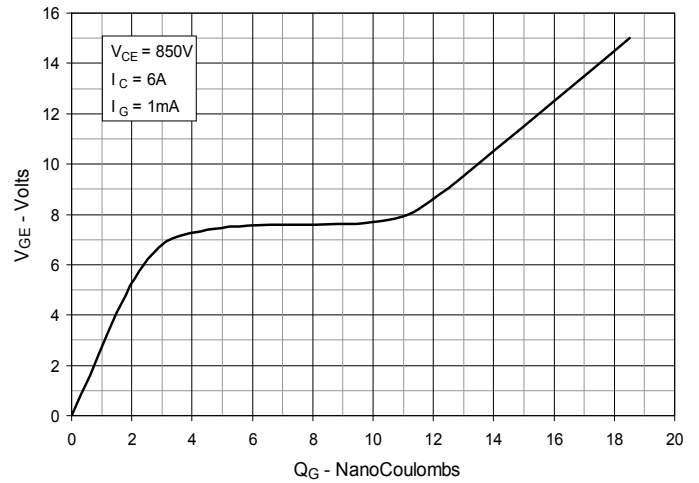


Fig. 9. Reverse-Bias Safe Operating Area

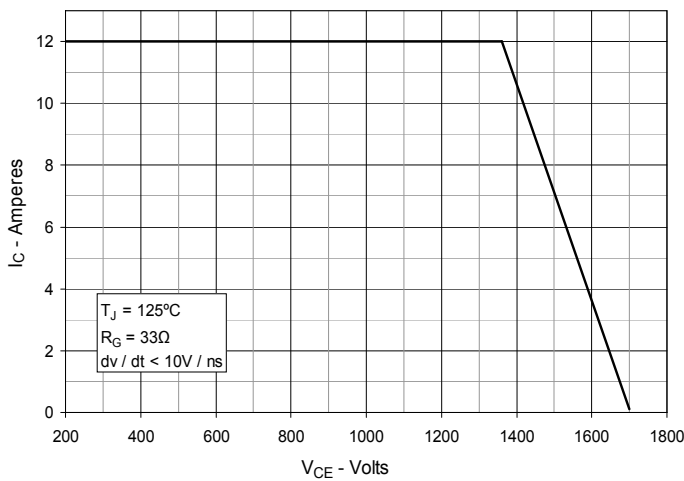


Fig. 10. Capacitance

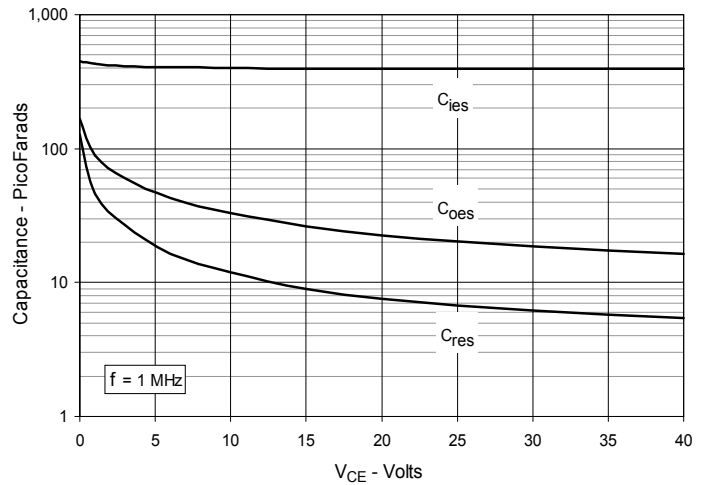


Fig. 11. Maximum Transient Thermal Impedance

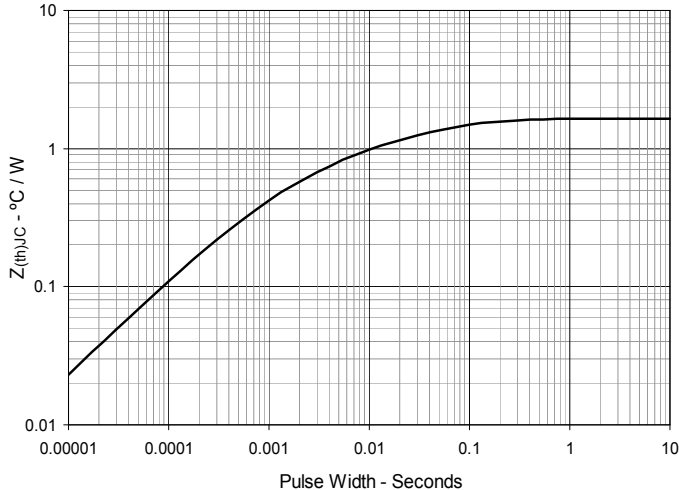


Fig. 12. Forward-Bias Safe Operating Area

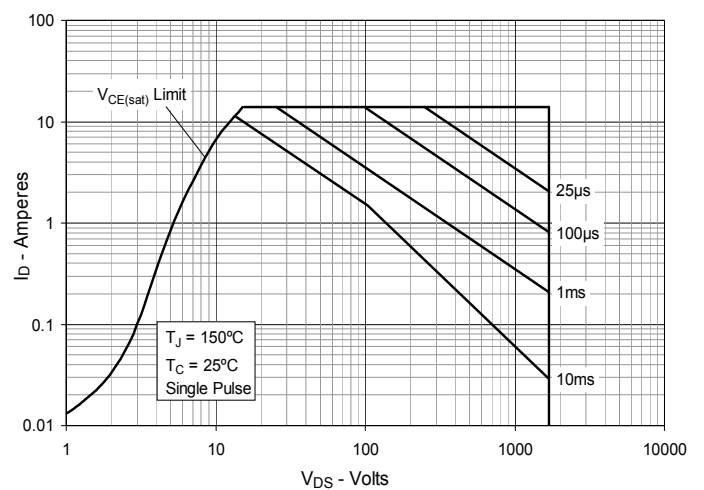


Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

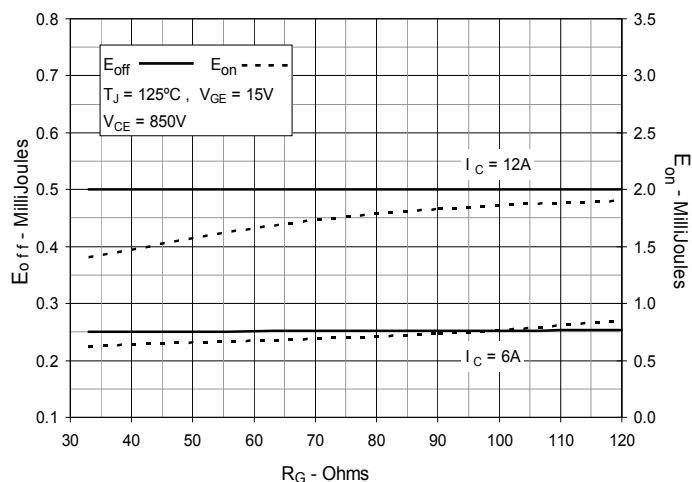


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

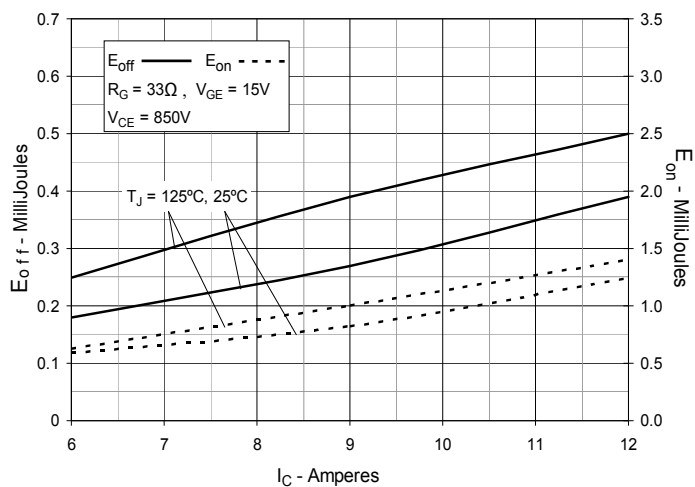
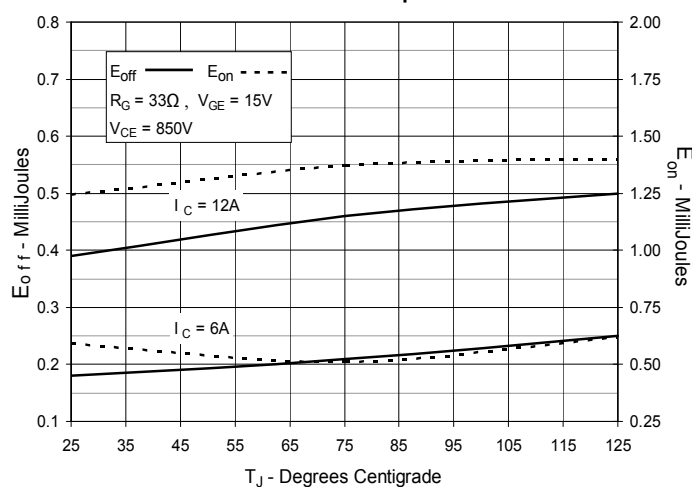


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature





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